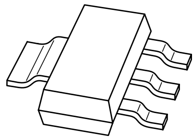


# PBSS9110Z

**100 V, 1 A PNP low $V_{CEsat}$ (BISS) transistor**

**Rev. 03 — 11 December 2009** **Product data sheet**

## 1. Product profile

### 1.1 General description

PNP low $V_{CEsat}$ Breakthrough In Small Signal (BISS) transistor in a SOT223 (SC-73) small Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS8110Z.

### 1.2 Features

- Low collector-emitter saturation voltage $V_{CEsat}$
- High collector current capability $I_C$ and $I_{CM}$
- High collector current gain ($h_{FE}$) at high $I_C$
- High efficiency due to less heat generation
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors

### 1.3 Applications

- High-voltage DC-to-DC conversion
- High-voltage MOSFET gate driving
- High-voltage motor control
- High-voltage power switches (e.g. motors, fans)
- Automotive applications

### 1.4 Quick reference data

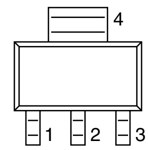
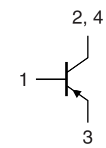
**Table 1. Quick reference data**

| Symbol | Parameter | Conditions | | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|---|
| $V_{CEO}$ | collector-emitter voltage | open base | | - | - | –100 | V |
| $I_C$ | collector current | | | - | - | –1 | A |
| $I_{CM}$ | peak collector current | single pulse; $t_p \leq 1$ ms | | - | - | –3 | A |
| $R_{CEsat}$ | collector-emitter saturation resistance | $I_C = –1$ A; $I_B = –100$ mA | [1] | - | 170 | 320 | mΩ |

[1] Pulse test: $t_p \leq 300$ μs; $\delta \leq 0.02$.

## 2. Pinning information

**Table 2. Pinning**

| Pin | Description | Simplified outline | Symbol |
|---|---|---|---|
| 1 | base |  |  |
| 2 | collector | | |
| 3 | emitter | | |
| 4 | collector | | |





## 3. Ordering information

**Table 3. Ordering information**

| Type number | Package | | |
|---|---|---|---|
| | Name | Description | Version |
| PBSS9110Z | SC-73 | plastic surface-mounted package with increased heat sink; 4 leads | SOT223 |

## 4. Marking

**Table 4. Marking codes**

| Type number | Marking code |
|---|---|
| PBSS9110Z | PB9110 |

## 5. Limiting values

**Table 5. Limiting values**

*In accordance with the Absolute Maximum Rating System (IEC 60134).*

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|---|---|---|---|---|---|---|
| $V_{CBO}$ | collector-base voltage | open emitter | | - | –120 | V |
| $V_{CEO}$ | collector-emitter voltage | open base | | - | –100 | V |
| $V_{EBO}$ | emitter-base voltage | open collector | | - | –5 | V |
| $I_C$ | collector current | | | - | –1 | A |
| $I_{CM}$ | peak collector current | single pulse; $t_p \leq 1$ ms | | - | –3 | A |
| $I_B$ | base current | | | - | –0.3 | A |
| $P_{tot}$ | total power dissipation | $T_{amb} \leq 25$ °C | [1] | - | 0.65 | W |
| | | | [2] | - | 1 | W |
| | | | [3] | - | 1.4 | W |

**Table 5. Limiting values** *…continued*

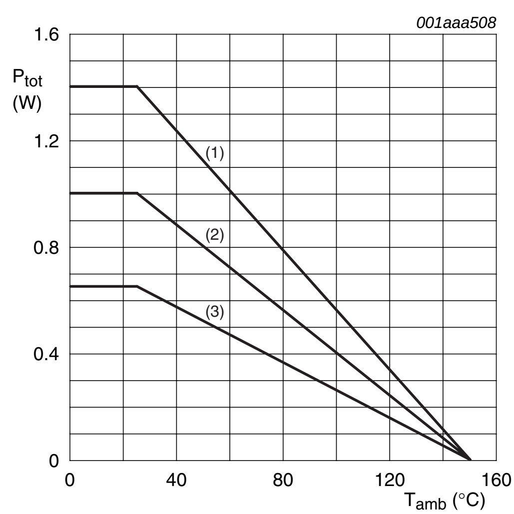
*In accordance with the Absolute Maximum Rating System (IEC 60134).*

| Symbol | Parameter | Conditions | Min | Max | Unit |
|---|---|---|---|---|---|
| $T_j$ | junction temperature | | - | 150 | °C |
| $T_{amb}$ | ambient temperature | | –65 | +150 | °C |
| $T_{stg}$ | storage temperature | | –65 | +150 | °C |

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1cm$^2$.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6cm$^2$.




(1) FR4 PCB, mounting pad for collector 6cm$^2$

(2) FR4 PCB, mounting pad for collector 1cm$^2$

(3) FR4 PCB, standard footprint

**Fig 1. Power derating curves**

## 6. Thermal characteristics

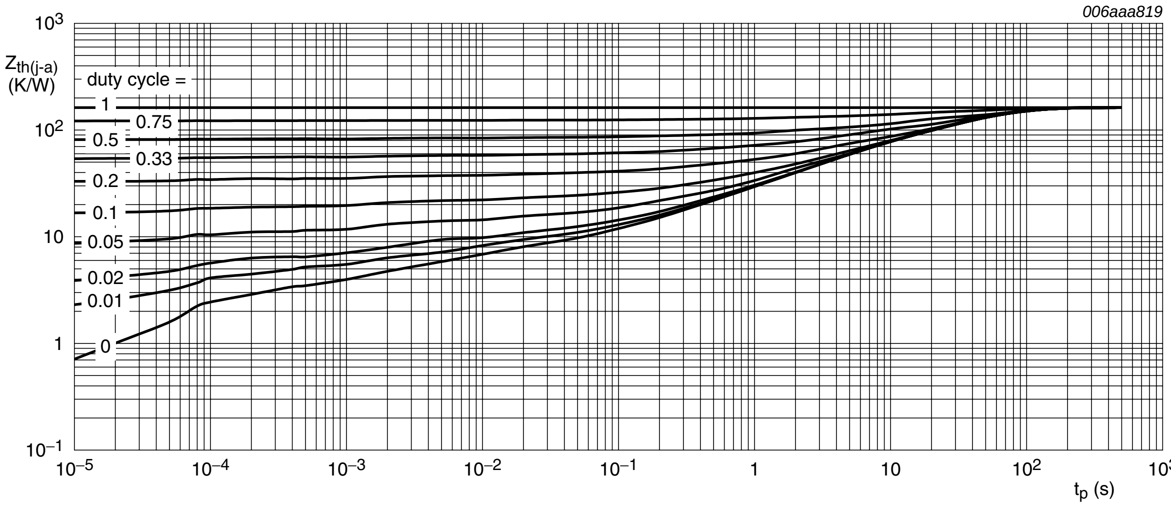
**Table 6. Thermal characteristics**

| Symbol | Parameter | Conditions | | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|---|
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | in free air | [1] | - | - | 192 | K/W |
| | | | [2] | - | - | 125 | K/W |
| | | | [3] | - | - | 89 | K/W |
| $R_{th(j-sp)}$ | thermal resistance from junction to solder point | | | - | - | 17 | K/W |

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

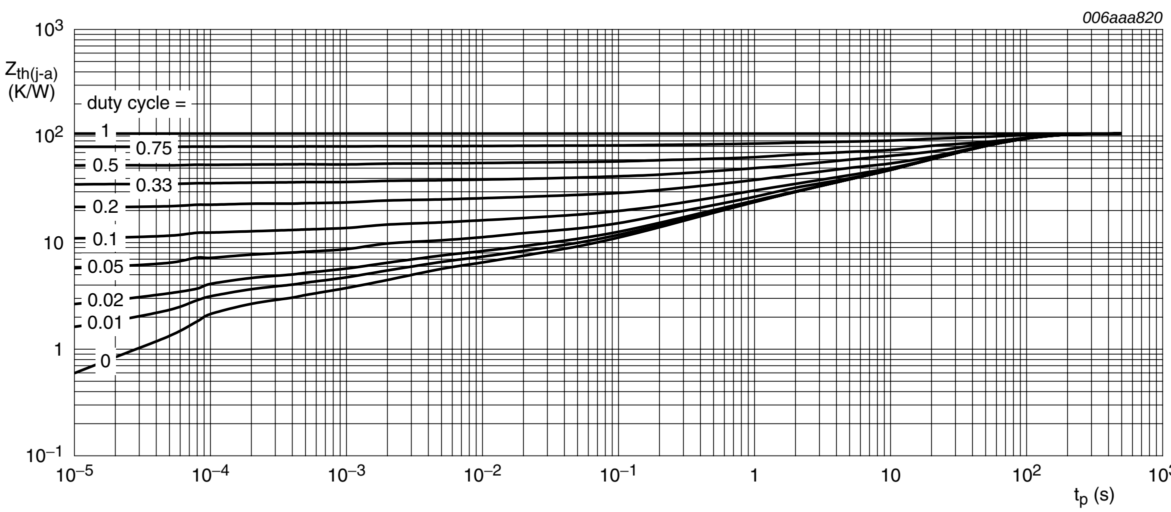
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1cm$^2$.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6cm$^2$.



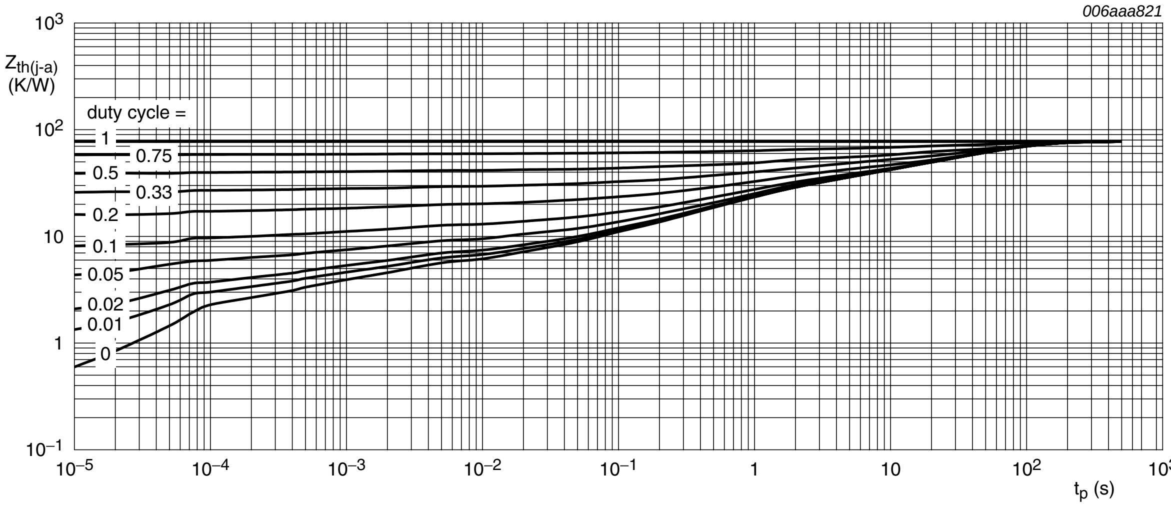

FR4 PCB, standard footprint

**Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values**




FR4 PCB, mounting pad for collector 1cm$^2$

**Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values**




FR4 PCB, mounting pad for collector 6cm$^2$

**Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values**

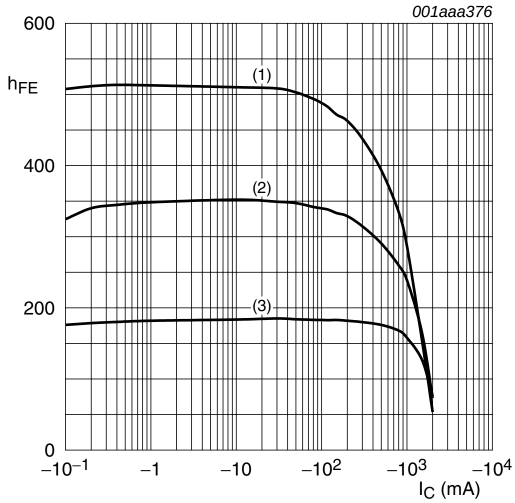
# 7. Characteristics

**Table 7. Characteristics**

*$T_{amb}$ = 25 °C unless otherwise specified.*

| Symbol | Parameter | Conditions | | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|---|
| $I_{CBO}$ | collector-base cut-off current | $V_{CB}$ = –80 V; $I_E$ = 0 A | | - | - | –100 | nA |
| | | $V_{CB}$ = –80 V; $I_E$ = 0 A; $T_j$ = 150 °C | | - | - | –50 | μA |
| $I_{CES}$ | collector-emitter cut-off current | $V_{CE}$ = –80 V; $V_{BE}$ = 0 V | | - | - | –100 | nA |
| $I_{EBO}$ | emitter-base cut-off current | $V_{EB}$ = –4 V; $I_C$ = 0 A | | - | - | –100 | nA |
| $h_{FE}$ | DC current gain | $V_{CE}$ = –5 V; $I_C$ = –1 mA | | 150 | - | - | |
| | | $V_{CE}$ = –5 V; $I_C$ = –250 mA | | 150 | - | - | |
| | | $V_{CE}$ = –5 V; $I_C$ = –0.5 A | [1] | 150 | - | 450 | |
| | | $V_{CE}$ = –5 V; $I_C$ = –1 A | [1] | 125 | - | - | |
| $V_{CEsat}$ | collector-emitter saturation voltage | $I_C$ = –250 mA; $I_B$ = –25 mA | | - | - | –120 | mV |
| | | $I_C$ = –500 mA; $I_B$ = –50 mA | [1] | - | - | –180 | mV |
| | | $I_C$ = –1 A; $I_B$ = –100 mA | [1] | - | - | –320 | mV |
| $R_{CEsat}$ | collector-emitter saturation resistance | $I_C$ = –1 A; $I_B$ = –100 mA | [1] | - | 170 | 320 | mΩ |
| $V_{BEsat}$ | base-emitter saturation voltage | $I_C$ = –1 A; $I_B$ = –100 mA | [1] | - | - | –1.1 | V |
| $V_{BEon}$ | base-emitter turn-on voltage | $V_{CE}$ = –5 V; $I_C$ = –1 A | [1] | - | - | –1.0 | V |
| $t_d$ | delay time | $V_{CC}$ = –10 V; $I_C$ = –0.5 A; $I_{Bon}$ = –0.025 A; $I_{Boff}$ = 0.025 A | | - | 20 | - | ns |
| $t_r$ | rise time | | | - | 60 | - | ns |
| $t_{on}$ | turn-on time | | | - | 80 | - | ns |
| $t_s$ | storage time | | | - | 290 | - | ns |
| $t_f$ | fall time | | | - | 120 | - | ns |
| $t_{off}$ | turn-off time | | | - | 410 | - | ns |
| $f_T$ | transition frequency | $V_{CE}$ = –10 V; $I_C$ = –50 mA; f = 100 MHz | | 100 | - | - | MHz |
| $C_c$ | collector capacitance | $V_{CB}$ = –10 V; $I_E$ = $i_e$ = 0 A; f = 1 MHz | | - | - | 17 | pF |

[1] Pulse test: $t_p \leq 300$ μs; $\delta \leq 0.02$.



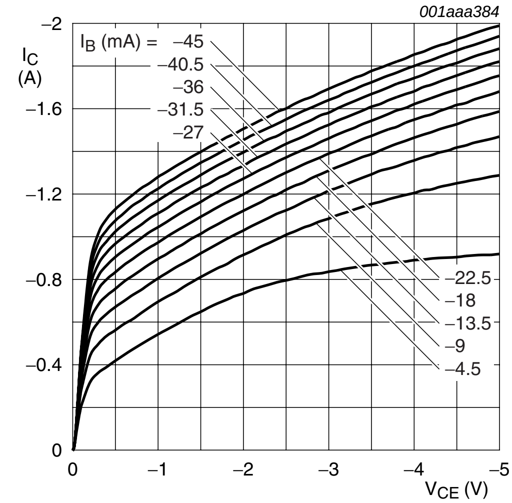

$V_{CE} = -10$ V

(1) $T_{amb} = 100$ °C

(2) $T_{amb} = 25$ °C

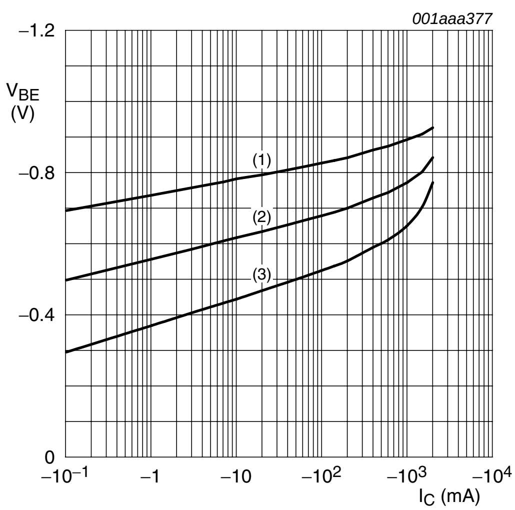
(3) $T_{amb} = -55$ °C

**Fig 5. DC current gain as a function of collector current; typical values**




$T_{amb} = 25$ °C

**Fig 6. Collector current as a function of collector-emitter voltage; typical values**



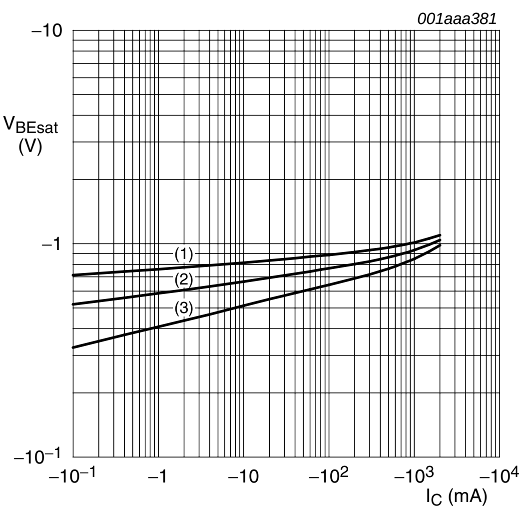

$V_{CE} = -10$ V

(1) $T_{amb} = -55$ °C

(2) $T_{amb} = 25$ °C

(3) $T_{amb} = 100$ °C

**Fig 7. Base-emitter voltage as a function of collector current; typical values**



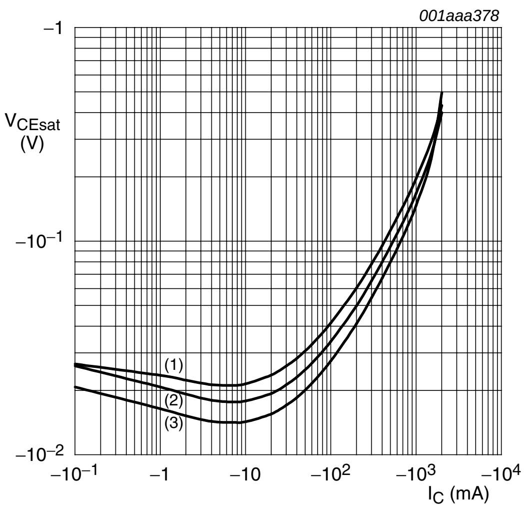

$I_C/I_B = 10$

(1) $T_{amb} = -55$ °C

(2) $T_{amb} = 25$ °C

(3) $T_{amb} = 100$ °C

**Fig 8. Base-emitter saturation voltage as a function of collector current; typical values**



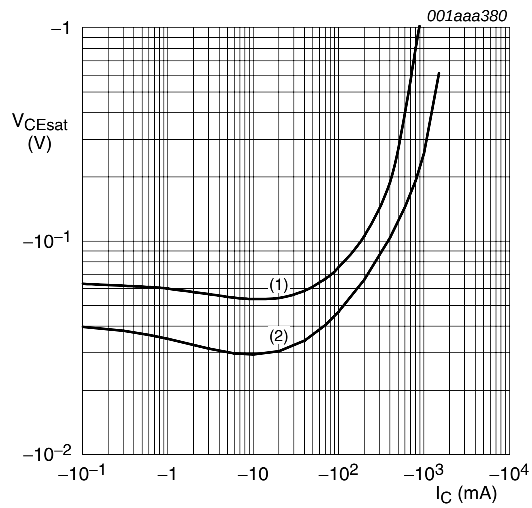

$I_C/I_B = 10$

(1) $T_{amb}$ = 100 °C

(2) $T_{amb}$ = 25 °C

(3) $T_{amb}$ = −55 °C

**Fig 9. Collector-emitter saturation voltage as a function of collector current; typical values**

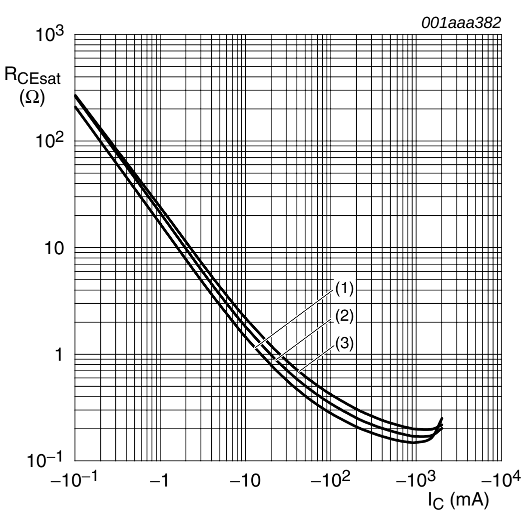



$T_{amb}$ = 25 °C

(1) $I_C/I_B = 50$

(2) $I_C/I_B = 20$

**Fig 10. Collector-emitter saturation voltage as a function of collector current; typical values**



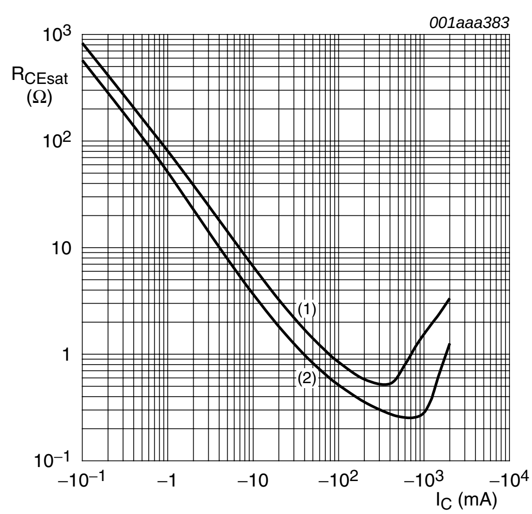

$I_C/I_B = 10$

(1) $T_{amb}$ = −55 °C

(2) $T_{amb}$ = 25 °C

(3) $T_{amb}$ = 100 °C

**Fig 11. Collector-emitter saturation resistance as a function of collector current; typical values**




$T_{amb}$ = 25 °C

(1) $I_C/I_B = 50$

(2) $I_C/I_B = 20$

**Fig 12. Collector-emitter saturation resistance as a function of collector current; typical values**

# 8. Test information

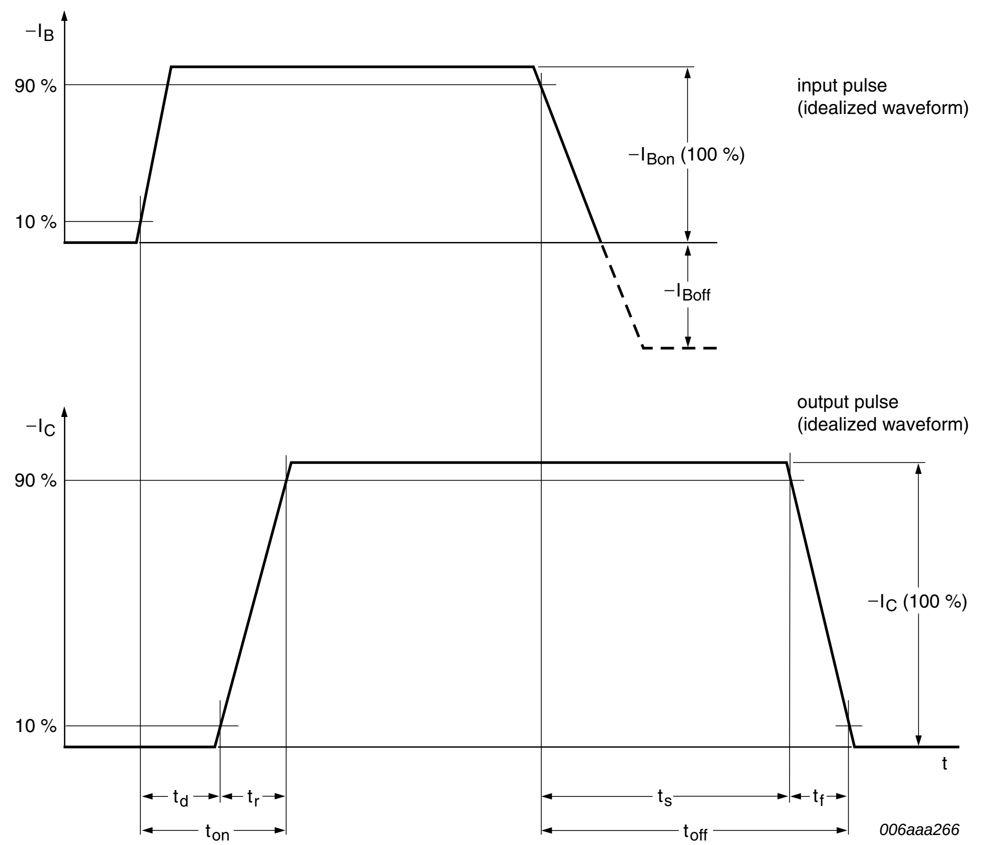
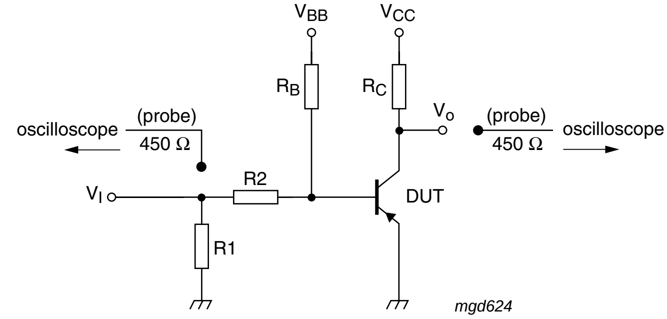



**Fig 13. BISS transistor switching time definition**




$V_{CC}$ = –10 V; $I_C$ = –0.5 A; $I_{Bon}$ = –0.025 A; $I_{Boff}$ = 0.025 A

**Fig 14. Test circuit for switching times**

## 9. Package outline

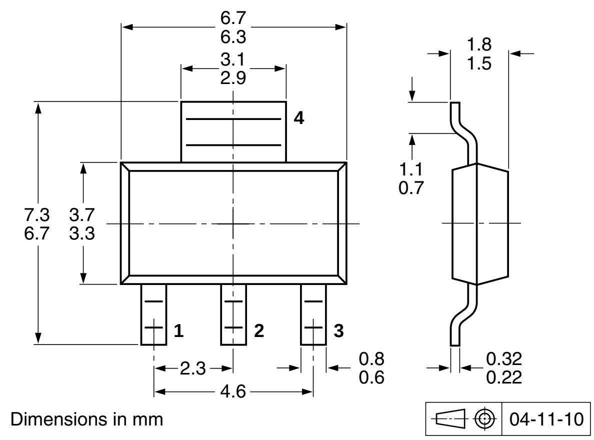



Fig 15. Package outline SOT223 (SC-73)

## 10. Packing information

Table 8. Packing methods

*The indicated -xxx are the last three digits of the 12NC ordering code.*[1]

| Type number | Package | Description | Packing quantity | |
|---|---|---|---|---|
| | | | 1000 | 4000 |
| PBSS9110Z | SOT223 | 8 mm pitch, 12 mm tape and reel | -115 | -135 |

[1] For further information and the availability of packing methods, see Section 14.

## 11. Soldering

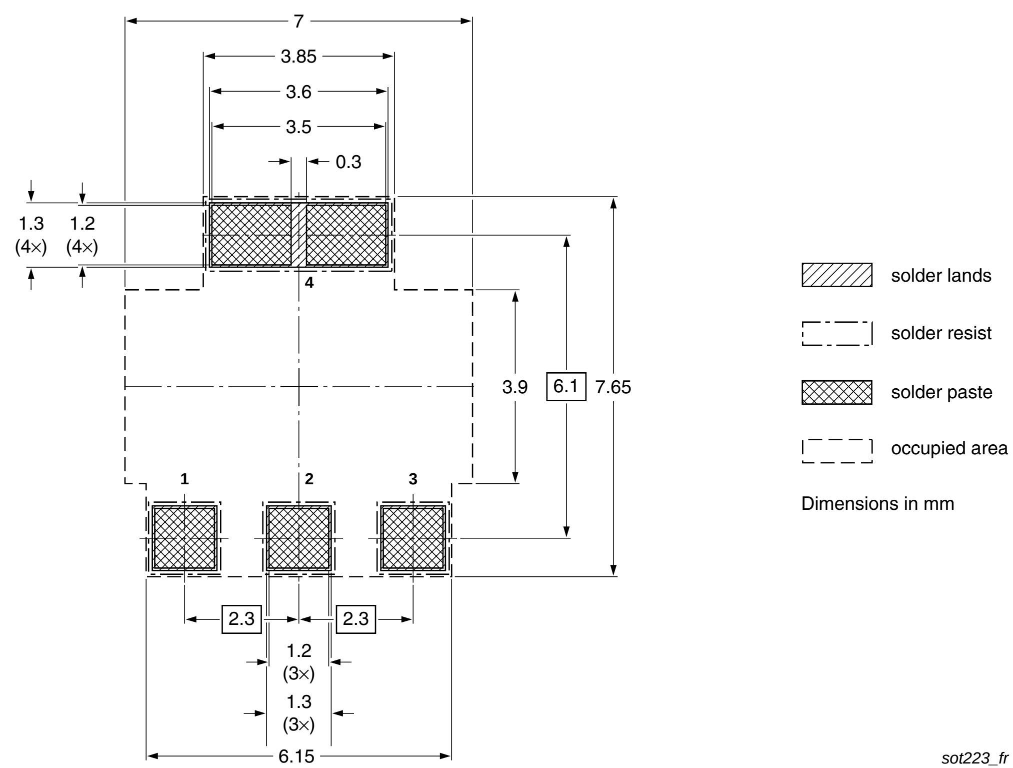



Fig 16. Reflow soldering footprint SOT223 (SC-73)

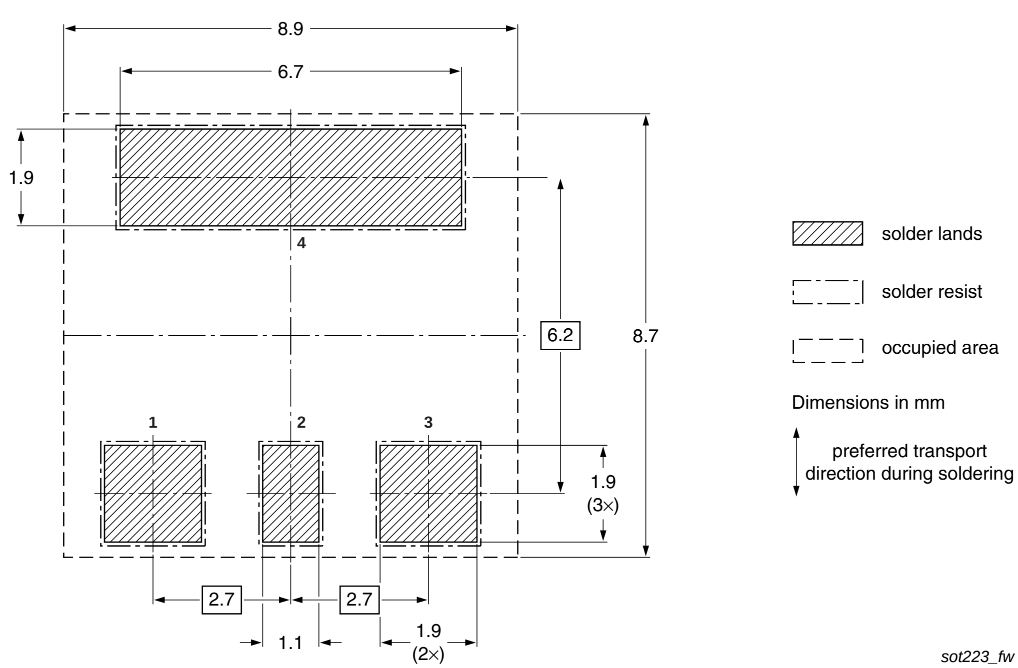



Fig 17. Wave soldering footprint SOT223 (SC-73)

## 12. Revision history

**Table 9. Revision history**

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|---|---|---|---|---|
| PBSS9110Z_3 | 20091211 | Product data sheet | - | PBSS9110Z_2 |
| Modifications: | • This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content. • Figure 16 "Reflow soldering footprint SOT223 (SC-73)": updated • Figure 17 "Wave soldering footprint SOT223 (SC-73)": updated | | | |
| PBSS9110Z_2 | 20060724 | Product data sheet | - | PBSS9110Z_1 |
| PBSS9110Z_1 | 20040609 | Product data sheet | - | - |

# 13. Legal information

## 13.1 Data sheet status

| Document status[1][2] | Product status[3] | Definition |
|---|---|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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For more information, please visit: **http://www.nxp.com**

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## 15. Contents





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**Document identifier: PBSS9110Z_3**